

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

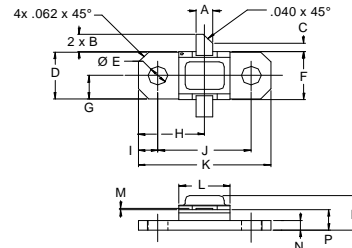
The **ASI AJT006** is Designed for

**FEATURES:**

- Input Matching Network
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	0.9 A
<b>V<sub>CC</sub></b>	32V
<b>P<sub>DISS</sub></b>	25 W @ T <sub>C</sub> ≤ 75 °C
<b>T<sub>J</sub></b>	-65 °C to +250 °C
<b>T<sub>STG</sub></b>	-65 °C to +200 °C
<b>θ<sub>JC</sub></b>	7.0 °C/W

**PACKAGE STYLE .310 2L FLG**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.095 / 2.41	.105 / 2.67
B	.100 / 2.54	.120 / 3.05
C	.050 / 1.27	
D	.286 / 7.26	.306 / 7.77
E	.110 / 2.79	.130 / 3.30
F	.306 / 7.77	.318 / 8.08
G	.148 / 3.76	
H	.400 / 10.16	
I	.119 / 3.02	
J	.552 / 14.02	.572 / 14.53
K	.790 / 20.07	.810 / 20.57
L	.300 / 7.62	.320 / 8.13
M	.003 / 0.08	.006 / 0.15
N	.052 / 1.32	.072 / 1.83
P	.118 / 3.00	.131 / 3.33
R	.230 / 5.84	

**ORDER CODE: ASI10544**
**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CBO</sub></b>	I <sub>C</sub> = 1 mA	48			<b>V</b>
<b>BV<sub>CER</sub></b>	I <sub>C</sub> = 5 mA      R <sub>BE</sub> = 10 Ω	48			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 1 mA	3.5			<b>V</b>
<b>I<sub>CES</sub></b>	V <sub>CE</sub> = 28 V			0.5	<b>mA</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V      I <sub>C</sub> = 250 mA	30		300	<b>---</b>
<b>P<sub>G</sub></b>	V <sub>CC</sub> = 45 V      P <sub>OUT</sub> = 6.0 W      f = 960-1215 MHz	9.3			<b>dB</b>
<b>η<sub>C</sub></b>		40			<b>%</b>